

Ji Su Han

List of Publications by Year in descending order

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Version: 2024-02-01

20
papers

1,394
citations

687363

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794594

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docs citations

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times ranked

1455
citing authors

#	ARTICLE	IF	CITATIONS
1	High Hole Mobility Inorganic Halide Perovskite Field-Effect Transistors with Enhanced Phase Stability and Interfacial Defect Tolerance. <i>Advanced Electronic Materials</i> , 2022, 8, 2100624.	5.1	6
2	Vertically aligned two-dimensional halide perovskites for reliably operable artificial synapses. <i>Materials Today</i> , 2022, 52, 19-30.	14.2	40
3	Strong Fermi-level pinning at metal contacts to halide perovskites. <i>Journal of Materials Chemistry C</i> , 2021, 9, 15212-15220.	5.5	12
4	Resistive Switching Memory: Lead-Free Dual-Phase Halide Perovskites for Preconditioned Conducting-Bridge Memory (Small 41/2020). <i>Small</i> , 2020, 16, 2070228.	10.0	0
5	Lead-Free Dual-Phase Halide Perovskites for Preconditioned Conducting-Bridge Memory. <i>Small</i> , 2020, 16, e2003225.	10.0	27
6	Quasi-2D halide perovskites for resistive switching devices with ON/OFF ratios above 109. <i>NPG Asia Materials</i> , 2020, 12, .	7.9	71
7	Dual-Phase All-Inorganic Cesium Halide Perovskites for Conducting-Bridge Memory-Based Artificial Synapses. <i>Advanced Functional Materials</i> , 2019, 29, 1906686.	14.9	79
8	Lead-Free All-Inorganic Cesium Tin Iodide Perovskite for Filamentary and Interface-Type Resistive Switching toward Environment-Friendly and Temperature-Tolerant Nonvolatile Memories. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 8155-8163.	8.0	133
9	Halide perovskites for resistive random-access memories. <i>Journal of Materials Chemistry C</i> , 2019, 7, 5226-5234.	5.5	90
10	Conducting Bridge Resistive Switching Behaviors in Cubic MAPbI_3 , Orthorhombic RbPbI_3 , and Their Mixtures. <i>Advanced Electronic Materials</i> , 2019, 5, 1800586.	5.1	33
11	Data Storage: Air-Stable Cesium Lead Iodide Perovskite for Ultra-Low Operating Voltage Resistive Switching (<i>Adv. Funct. Mater.</i> 5/2018). <i>Advanced Functional Materials</i> , 2018, 28, 1870029.	14.9	4
12	Halide Perovskites for Applications beyond Photovoltaics. <i>Small Methods</i> , 2018, 2, 1700310.	8.6	94
13	Air-Stable Cesium Lead Iodide Perovskite for Ultra-Low Operating Voltage Resistive Switching. <i>Advanced Functional Materials</i> , 2018, 28, 1705783.	14.9	177
14	Recent Advances in Memristive Materials for Artificial Synapses. <i>Advanced Materials Technologies</i> , 2018, 3, 1800457.	5.8	161
15	Halide Perovskites: Organic-Inorganic Hybrid Halide Perovskites for Memories, Transistors, and Artificial Synapses (<i>Adv. Mater.</i> 42/2018). <i>Advanced Materials</i> , 2018, 30, 1870317.	21.0	7
16	Organic-Inorganic Hybrid Halide Perovskites for Memories, Transistors, and Artificial Synapses. <i>Advanced Materials</i> , 2018, 30, e1704002.	21.0	205
17	Wafer-scale reliable switching memory based on 2-dimensional layered organic-inorganic halide perovskite. <i>Nanoscale</i> , 2017, 9, 15278-15285.	5.6	113
18	Enhanced Endurance Organolead Halide Perovskite Resistive Switching Memories Operable under an Extremely Low Bending Radius. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 30764-30771.	8.0	135

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19	Electrical Properties of Metal-Induced Laterally Crystallized p-Type LTPS-TFT With High- κ ZrTiO ₄ Gate Dielectric Featuring Low Equivalent-Oxide-Thickness. IEEE Transactions on Electron Devices, 2016, 63, 2391-2397.	3.0	4
20	Progress of p-channel bottom-gate poly-Si thin-film transistor by nickel silicide seed-induced lateral crystallization. Applied Physics A: Materials Science and Processing, 2016, 122, 1.	2.3	3